Jan. 8, 1974 N. E. COLLINS ET AL Re. 27,879

OHMIC CONTACT FOR GROUP III-V P-TYPE SEMICONDUCTORS

Original Filed Dec. 28, 1970

Fig. 1.

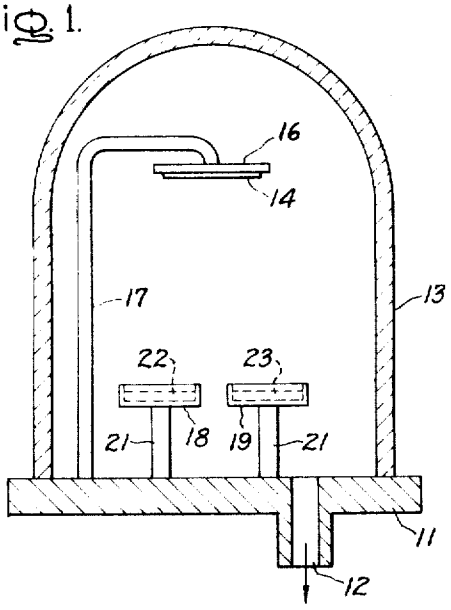


Fig. 3.

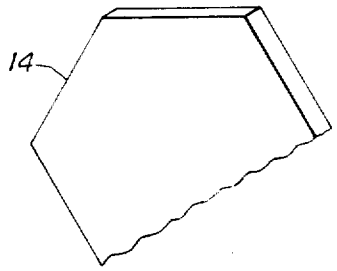


Fig. 4.

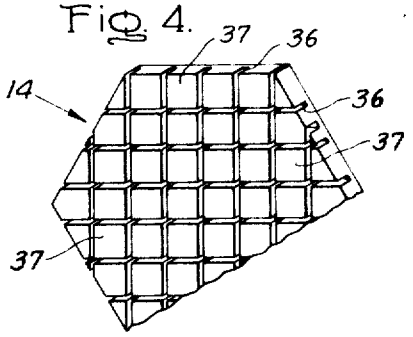


Fig. 2.

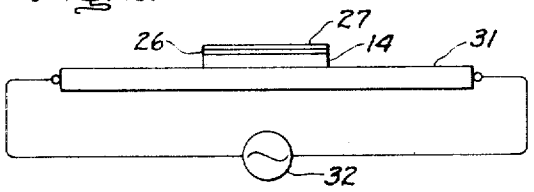


Fig. 5.

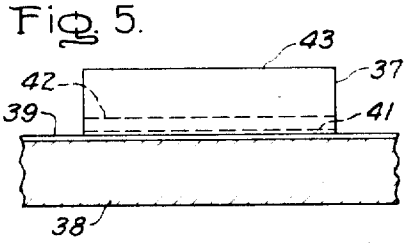


Fig. 7.

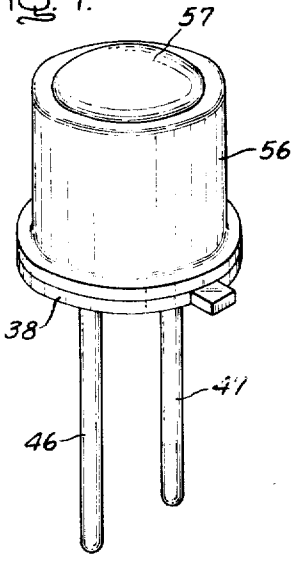
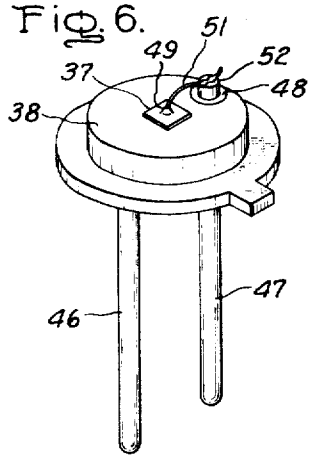


Fig. 6.



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United States Patent Office

Re. 27,879
Reissued Jan. 8, 1974

27,879

OHMIC CONTACT FOR GROUP III–V p-TYPE SEMICONDUCTORS

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Original No. 3,684,930, dated Aug. 15, 1972, Ser. No. 101,971, Dec. 28, 1970. Application for reissue Feb. 21, 1973, Ser. No. 334,237

Int. Cl. H01l *1/14*

U.S. Cl. 317—234 R 14 Claims

Matter enclosed in heavy brackets [ ] appears in the original patent but forms no part of this reissue specification; matter printed in italics indicates the additions made by reissue.

ABSTRACT OF THE DISCLOSURE

A combination of gold-germanium or gold-silicon alloy and zinc or other metallic Group II element provides an electrical contact and low-temperature bonding material for p-type semiconductors of Group III–V such as gallium arsenide.

BACKGROUND OF THE INVENTION

The invention is in the field of making ohmic contacts on semiconductor materials, and bonding the ohmic contact to a header. More particularly, the invention relates to ohmic contacts and bonding for Group III–V p-type semiconductors such as gallium arsenide.

Light-emitting diodes, i.e., solid-state lamps, are one type of device, among others, which make use of p-type semiconductor material. A light-emitting diode may comprise a p-n junction, which emits light when current is passed therethrough, formed at the junction of p-type and an n-type semiconductor material such as gallium arsenide. The p-type and n-type regions are formed by doping the basic material with certain impurities in a suitable process, such as diffusion or epitaxial growth. In manufacture, a thin wafer of the basic material, such as gallium arsenide, is processed to form a p-n junction between and parallel to the larger faces of the wafer, and the wafer is then severed into a plurality of pellets each pellet containing a p-n junction. Each pellet is then assembled into a lamp housing, making suitable electrical connections to the p-side and n-side thereof so that current can be made to flow through the p-n junction for causing light to be emitted. One way of accomplishing this is to place the pellet, p-side down, on a gold-plated Kovar header, and heat to over 500° C. to cause the pellet to fuse to the gold-plated header. A small "dot" contact is made to the n-side of the pellet, to complete the electrical connections; the header provides electrical connection to the p-side of the pellet. The aforesaid heating of the assembly to fuse the pellet to the header undesirably tends to reduce the light-emitting capability of the diode, and reduction of the temperature employed for the fusing tends to result in unsatisfactory bonding of the diode pellet to the header.

SUMMARY OF THE INVENTION

Objects of the invention are to provide an improved electrical contact and bonding material and method for p-type Group III–V semiconductors, and to make the electrical contact and bonding by the use of lower temperatures than heretofore.

The invention comprises, briefly and in a preferred embodiment, a contact and bonding material for p-type Group III–V semiconductors, such as gallium arsenide, comprising a combination of gold-germanium or gold-silicon alloy (preferably the eutectic) and a Group II metallic element such as zinc. Preferably, the Group II metallic element is zinc and is about 1 to 15 percent by weight of the gold-germanium eutectic alloy. A preferred method of manufacture comprises the steps of depositing a layer of gold-germanium eutectic alloy onto a p-type surface of a wafer of Group III–V semiconductor material, depositing a layer of a Group II metallic element over the eutectic alloy layer, heating to sinter the deposited layers into the p-type surface of the wafer, severing the wafer into pellets, placing a pellet p-side down on a gold-plated header, and heating momentarily to fuse the pellet to the header.

BRIEF DESCRIPTION OF THE DRAWING

FIG. 1 is a cross-sectional view of a vacuum evaporation chamber, in which the electrical contact and bonding material of the invention is formed on a p-surface of a semiconductor wafer;

FIG. 2 is a side view showing the wafer, with evaporated materials thereon, being heated on an electrically heated strip heater;

FIG. 3 is a perspective view of the wafer after the deposited materials have been fused into the p-surface thereof as illustrated in FIG. 2;

FIG. 4 is a perspective view of the wafer after the surface thereof has been scribed so that the wafer may be severed into a plurality of pellets;

FIG. 5 is a side view of a pellet, placed p-side down on a header;

FIG. 6 is a perspective view of the pellet on a header; and

FIG. 7 is a perspective view of a solid-state lamp having a lens housing attached to the header assembly of FIG. 6.

DESCRIPTION OF THE PREFERRED EMBODIMENT

The vacuum evaporation apparatus of FIG. 1 consists of a base plate **11** provided with a vacuum port **12**, and a cover **13**, preferably of glass, which fits onto the base **11** in a vacuum tight manner. A wafer **14** having a p-type surface of Group III–V, such as gallium arsenide, gallium phosphide, or gallium arsenide phosphide, is supported, p-surface down, by means of being clamped or otherwise attached to a support plate **16** which is positioned within the vacuum chamber by means of a bracket **17** attached to the base **11**. A pair of boats **18** and **19** are supported from the base **11** by means of posts **21** which provide electrical and thermal insulation of the boats **18**, **19** from the base **11**. Preferably the boats **18** and **19** are made of metal and are arranged to be heated by passing electrical current directly through the metal of the boats. One of the boats **18** carries gold-germanium or gold-silicon alloy **22**, and the other boat **19** carries a Group II metallic element, such as zinc of high purity (such as 99.999 percent purity). Preferably the aforesaid alloy is a eutectic, although in the case of gold-germanium alloy the amount of germanium can be from about 5 to 25 percent by weight of the alloy, and in the case of gold-silicon alloy the amount of silicon can be from about 4 to 10 percent by weight of the alloy.

The apparatus is evacuated, and the boat **18** containing the gold-germanium alloy **22** is heated electrically or by other means, so as to cause a layer of the alloy to become deposited on the under surface of the wafer **14** on the p-side thereof, preferably to a thickness of about 8,000 to 20,000 angstroms. The boat **19**, containing the Group II metallic element such as zinc, then is heated so as to cause a layer of the Group II metallic element to become deposited against the alloy layer,

his second layer preferably being about 200 to 2,000 ngstroms in thickness, or about 1 to 15 percent by veight of the first-deposited layer.

The wafer **14**, carrying the first layer **26** of the eutec- ic alloy and the second layer **27** of the Group II metal- ic element, is placed on a strip heater **31**, as shown in IG. 2, with the deposited layers **26** and **27** on upper ide, and is heated by means of electrical current from current source **32**, in an inert or reducing atmosphere such as hydrogen or nitrogen) to a temperature of bout 450° C., momentarily, to sinter the layers **26** and 7 into the surface of the wafer **14**.

At this stage, the wafer may look somewhat as shown n FIG. 3, and then is scribed in a criss-cross manner as ndicated by the numerals **36** in FIG. 4 to define in- lividual pellets **37**, and then is severed to provide a plu- ality of individual pellets **37**. A pellet **37** is positioned, -side down, onto a gold-plated header, as shown in IG. 5, in which the header **38**, which may be of Kovar, s plated with a layer of gold **39**. The dashed line **41** in- licates the depth of penetration into the pellet **37** of he composition of gold-germanium eutectic alloy and Group II metallic element, as has been described above. Assuming that the wafer **37** contains a p-n junction, this unction would be located approximately as indicated by he dashed line **42**, the upper portion **43** of the wafer **37** eing of n-type material.

The header **38** and pellet **37**, as shown in FIG. 5, are hen heated by any convenient means, such as in a fur- ace or by placing the header **38** on a strip heater, in an nert or reducing atmosphere (such as hydrogen or itrogen) to a temperature between 400° and 500° C., nomentarily, to fuse the pellet **37** to the gold-plating 9 of the header **38**, which is accomplished due to melt- ng of the composition material which has been sintered nto the p-surface of the pellet as described above.

FIG. 6 shows a typical header **38**, with the pellet **37** onded thereto as described above. A first lead wire **46** is attached to the header **38**, and a second lead wire **47** extends through an opening in the header **38** and is at- tached to and insulated from the header by means of an insulating material **48** such as glass. A "dot" size con- tact **49** is provided on the upper or n-surface of the pel- let **38**, by well known means, and a connector wire **51** is electrically and mechanically attached to the dot con- act **49** and the upper end **52** of the second connector wire **47**. A protective housing **56** may be positioned over nd attached to the header **38**, as shown in FIG. 7, and nay be provided with a lens **57** in an opening at the uter ends thereof, so that when the light-emitting diode wafer **37** emits light due to current being passed through he p-n junction **42** thereof by means of voltage applied o the lead wires **46** and **47**, the emitted light will be ocused by the lens **57** in a desired manner.

The electrical contact and bonding material com- position of the invention, comprising a combination of gold-germanium or gold-silicon alloy and a Group II metallic element, as described above, permits bonding of the pellet **37** to the header **38** at a lower tempera- ture, for example approximately 100° C. lower, than the temperature heretofore required for bonding p-type mate- rial directly to the gold plating **39** of the header **38**. At the same time, a bond of very high mechanical strength is achieved. Thus, good bonding is achieved at reduced temperature, thus reducing the likelihood of damaging the light-emitting capability of the p-n junction diode.

The method of the invention, by applying the electri- al contact and bonding material to the p-surface of the pellets **37**, permits temporary electrical connection to e made to the p-side, while another electrical contact s made to the "dot" contact **49** which has been previ- ously applied to the n-side of the diode in well known manner, so that the light emission capability and other characteristics of the diode can be measured before the diode is bonded to a header, whereby defective diodes

can be rejected before they are bonded to the relatively expensive header assembly.

The invention, in addition to achieving improved bonding at a lower temperature, also provides a highly desirable lower resistance of the connection between the p-surface and the header, resulting in increased efficiency, greater light output, and lower heating of the lamp during operation. The amounts of the gold-germanium alloy and the Group II metallic element, are not particularly critical, and good results have been obtained using the ranges of these materials as described above.

While preferred embodiments of the invention have been shown and described, various other embodiments and modifications thereof will become apparent to persons skilled in the art, and will fall within the scope of invention as defined in the following claims.

What we claim as new and desire to secure by Letters Patent of the United States is:

[1. An ohmic contact to a Group III–V p-type material, comprising a combination of gold-germanium or gold-silicon alloy and a Group II metallic element.]

[2. A contact as claimed in claim **1**, in which said alloy is a gold-germanium alloy having an amount of germanium that is about 5 to 25 percent by weight of the alloy.]

3. A contact as claimed in claim [1] *17*, in which said alloy is a gold-germanium eutectic.

4. A contact as claimed in claim [1] *17*, which said alloy is a gold-silicon alloy having an amount of silicon that is about 4 to 10 percent by weight of the alloy.

5. A contact as claimed in claim [1] *17*, in which said alloy is a gold-silicon eutectic.

6. A contact as claimed in claim [1] *17*, in which said alloy is a gold-germanium eutectic, and in which the Group II metallic element is zinc.

7. A contact as claimed in claim **6**, in which said alloy is a gold-germanium eutectic, and in which the amount of said zinc is about 1 to 15 percent by weight of said eutectic alloy.

8. A contact as claimed in claim [1] *17*, in which said Group III–V material is gallium arsenide, gallium phosphide, or gallium arsenide phosphide.

[9. A solid-state lamp comprising a Group III–V material having a p-n junction at the interface of a p-type region and an n-type region, and an ohmic contact at the surface of said p-type region comprising a combination of gold-germanium or gold-silicon alloy and a Group II metallic element.]

[10. A lamp as claimed in claim **9**, in which said alloy is a gold-germanium alloy having an amount of germanium that is about 5 to 25 percent by weight of the alloy.]

11. A lamp as claimed in claim [9] *18*, in which said alloy is a gold-germanium eutectic.

12. A lamp as claimed in claim [9] *18*, in which said alloy is a gold-silicon alloy having an amount of silicon that is about 4 to 10 percent by weight of the alloy.

13. A lamp as claimed in claim [9] *18*, in which said alloy is a gold-silicon eutectic.

14. A lamp as claimed in claim [9] *18*, in which said Group II metallic element is zinc.

15. A contact as claimed in claim **14**, in which said alloy is a gold-germanium eutectic, and in which the amount of said zinc is about 1 to 15 percent by weight of said eutectic alloy.

16. A lamp as claimed in claim [9] *18*, in which said Group III–V material is gallium arsenide, gallium phosphide, or gallium arsenide phosphide.

17. An ohmic contact to a Group III–V p-type material, comprising a combination of gold-germanium or gold-silicon alloy and a Group II metallic element, said gold-germanium alloy if present having an amount of germanium that is about 5 to 25 percent by weight of the alloy.

18. A solid-state lamp comprising a Group III–V material having a p-n junction at the interface of a p-type region and an n-type region, and an ohmic contact at the

surface of said p-type region comprising a combination of gold-germanium or gold-silicon alloy and a Group II metallic element, said gold-germanium alloy if present having an amount of germanium that is about 5 to 25 percent by weight of the alloy.

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MARTIN H. EDLOW, Primary Examiner

U.S. Cl. X.R.

317—235 N, 234 L, 234 N, 237